

TOSHIBA POWER TRANSISTOR MODULE SILICON NPN EPITAXIAL TYPE (DARLINGTON POWER TRANSISTOR 4 IN 1)

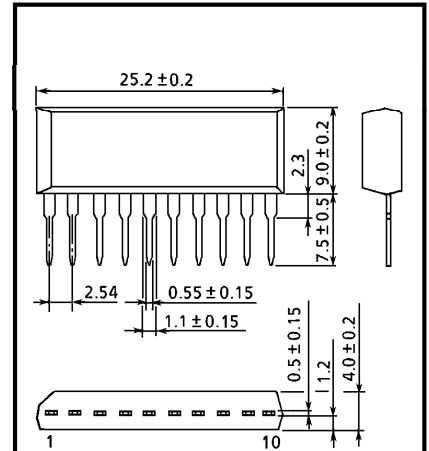
MP4101

HIGH POWER SWITCHING APPLICATIONS.
HAMMER DRIVE, PULSE MOTOR DRIVE.
INDUCTIVE LOAD SWITCHING.

INDUSTRIAL APPLICATIONS

Unit in mm

- Small Package by Full Molding (SIP 10 Pin)
- High Collector Power Dissipation (4 Devices Operation)
: $P_T = 4W$ ($T_a = 25^\circ C$)
- High Collector Current : I_C (DC) = 4A (Max.)
- High DC Current Gain : $h_{FE} = 2000$ (Min.) ($V_{CE} = 2V$, $I_C = 1A$)
- Zener Diode Included Between Collector and Base.



1, 10 EMITTER
2, 4, 6, 8 BASE
3, 5, 7, 9 COLLECTOR

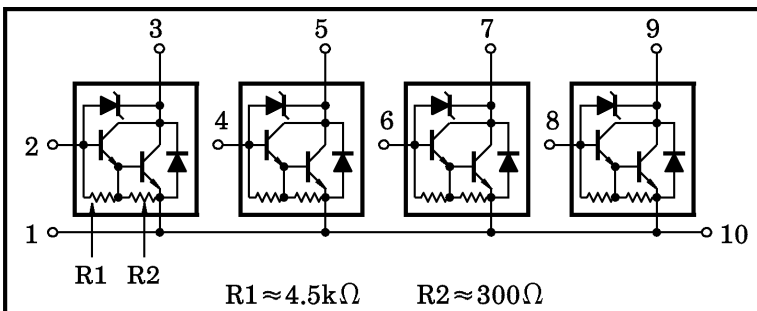
JEDEC	—
EIAJ	—
TOSHIBA	2-25A1A

Weight : 2.1g

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60 ± 10	V
Collector-Emitter Voltage	V_{CEO}	60 ± 10	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	DC	I_C	4
	Pulse	I_{CP}	6
Continuous Base Current	I_B	0.5	A
Collector Power Dissipation (1 Device Operation)	P_C	2.0	W
Collector Power Dissipation (4 Devices Operation)	P_T	4.0	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$

ARRAY CONFIGURATION



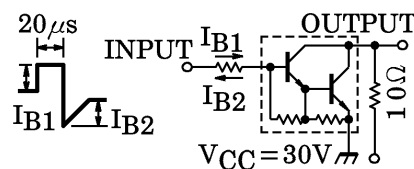
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HERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance of Junction to Ambient (4 Devices Operation, Ta=25°C)	$\Sigma R_{th(j-a)}$	31.3	°C/W
Maximum Lead Temperature for Soldering Purposes (3.2mm from Case for 10s)	T _L	260	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CBO}	V _{CB} = 45V, I _E = 0	—	—	10	μA
Collector Cut-off Current		I _{CEO}	V _{CE} = 45V, I _B = 0	—	—	10	μA
Emitter Cut-off Current		I _{EBO}	V _{EB} = 6V, I _C = 0	0.6	—	20	mA
Collector-Base Breakdown Voltage		V _{(BR)CBO}	I _C = 10mA, I _E = 0	50	60	70	V
Collector-Emitter Breakdown Voltage		V _{(BR)CEO}	I _C = 10mA, I _B = 0	50	60	70	V
DC Current Gain		h _{FE} (1)	V _{CE} = 2V, I _C = 1A	2000	—	15000	
		h _{FE} (2)	V _{CE} = 2V, I _C = 3A	1000	—	—	
Saturation Voltage	Collector-Emitter	V _{CE(sat)}	I _C = 3A, I _B = 10mA	—	—	1.5	V
	Base-Emitter	V _{BE(sat)}	I _C = 3A, I _B = 10mA	—	—	2.0	
Transition Frequency		f _T	V _{CE} = 2V, I _C = 0.5A	—	60	—	MHz
Collector Output Capacitance		C _{ob}	V _{CB} = 10V, I _E = 0A, f = 1MHz	—	30	—	pF
Switching Time	Turn-on Time	t _{on}	 <p>20 μs INPUT I_{B1} I_{B1} I_{B2} OUTPUT 10Ω V_{CC} = 30V</p> <p>I_{B1} = -I_{B2} = 10mA, DUTY CYCLE ≤ 1%</p>	—	0.2	—	μs
	Storage Time	t _{stg}		—	3.0	—	
	Fall Time	t _f		—	0.5	—	

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